

NCD30S10WG

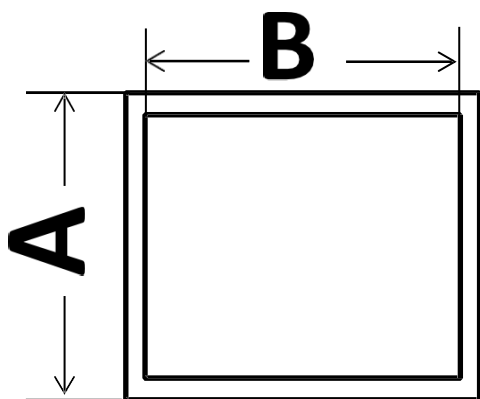
MOS-CONTROLLED RECTIFIER

Maximum Ratings(Per Leg) @T_A=25°C (unless otherwise specified)

| Parameter | Symbol | Ratings | Units |
|--|--------------------|---------|-------|
| Working Peak Reverse Voltage | V _{RWM} | 300 | V |
| Average Rectified Forward | I _{F(AV)} | 10.0 | A |
| Non-repetitive Peak Surge Current (8.3ms,half sine wave) Rated load (JEDEC METHOD) | I _{FSM} | 150 | A |
| Operating Junction Temperature | T _J | 175 | °C |
| Peak Repetitive Reverse Surge Current @2.0us, f=1KHz., T _J <175°C | I _{RRM} | 2.5 | A |
| Voltage Rate of Change | dv/dt | 10 | V/μS |

Electrical Characteristics @T_A=25°C

| Parameter | Symbol | Test Condition | MIN. | TYP. | MAX. | Units |
|-------------------------|-----------------|--|------|------|------|-------|
| Breakdown Voltage | V _{BR} | I _R = 250μA | 300 | - | - | V |
| Forward Voltage Drop | V _F | I _F = 10A | - | - | 0.97 | V |
| Reverse Leakage Current | I _R | T _A = 25°C, V _R = 300V | - | - | 10 | uA |
| | | T _A =150°C, V _R =300V | - | - | 5 | mA |



| Item | Information |
|---------------------|--------------------|
| Die Size (A) | 1701 μm 1701 μm |
| Active Die Size (B) | 1621 μm 1621 μm |
| Wafer Size | 8" |
| Gross Die | 9690 |
| Top Metal | Ag |
| Back Metal | Ag |
| Scribe Line Width | 40 μm |
| Wafer Thickness | 200 μm |